# **STL220N6F7**



# N-channel 60 V, 1.2 mΩ typ., 120 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

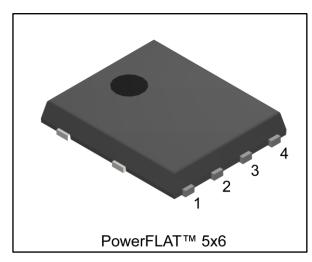
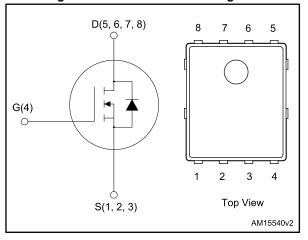


Figure 1: Internal schematic diagram



#### **Features**

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	ID
STL220N6F7	60 V	1.4 mΩ	120 A

- Among the lowest R<sub>DS(on)</sub> on the market
- Excellent FoM (figure of merit)
- Low C<sub>rss</sub>/C<sub>iss</sub> ratio for EMI immunity
- High avalanche ruggedness

### **Applications**

• Switching applications

### **Description**

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low onstate resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

**Table 1: Device summary** 

Order code	Marking	Package	Packaging
STL220N6F7	220N6F7	PowerFLAT™ 5x6	Tape and reel

Contents STL220N6F7

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STL220N6F7 Electrical ratings

# 1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage	60	V
$V_{GS}$	Gate-source voltage	±20	V
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 25 °C	120	Α
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 100 °C	120	Α
I <sub>DM</sub> <sup>(1)(2)</sup>	Drain current (pulsed)	480	Α
I <sub>D</sub> (3)	Drain current (continuous) at T <sub>pcb</sub> = 25 °C	40	Α
I <sub>D</sub> (3)	Drain current (continuous) at T <sub>pcb</sub> = 100 °C	28.5	Α
I <sub>DM</sub> <sup>(2)(3)</sup>	Drain current (pulsed)	160	Α
Eas	Single pulse avalanche energy (starting $T_j = 25$ °C, $I_{AS} = 20$ A)	900	mJ
P <sub>TOT</sub> <sup>(1)</sup>	Total dissipation at T <sub>C</sub> = 25 °C	188	W
P <sub>TOT</sub> (3)	Total dissipation at T <sub>pcb</sub> = 25 °C		W
т.	Operating junction temperature range	FF to 175	°C
Tj	Storage temperature range	-55 to 175	٠٠

#### Notes:

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-pcb</sub> <sup>(1)</sup>	Thermal resistance junction-pcb	31.3	°C/W
R <sub>thj-case</sub>	Thermal resistance junction-case	0.8	°C/W

#### Notes:

 $<sup>^{(1)}\!</sup>This$  value is rated according to  $R_{thj\text{-}c}$  .

<sup>&</sup>lt;sup>(2)</sup>Pulse width limited by safe operating area.

 $<sup>\</sup>ensuremath{^{(3)}}\xspace$  This value is rated according to  $R_{thj\text{-pcb}}.$ 

 $<sup>^{(1)}\!</sup>When$  mounted on FR-4 board of 1 inch², 2oz Cu, t < 10 s.

Electrical characteristics STL220N6F7

## 2 Electrical characteristics

(T<sub>C</sub> = 25 °C unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 1$ mA, $V_{GS} = 0$ V	60			V
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 60 V			1	μΑ
Igss	Gate-body leakage current	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V
R <sub>DS(on)</sub>	Static drain-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		1.2	1.4	mΩ

**Table 5: Dynamic** 

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Ciss	Input capacitance	V 05.V ( 4.MII.	ı	6500	1	pF
Coss	Output capacitance	$V_{DS} = 25 \text{ V, f} = 1 \text{ MHz,}$ $V_{GS} = 0 \text{ V}$	-	3200	-	pF
Crss	Reverse transfer capacitance	VGS - 0 V	ı	230	1	pF
$Q_g$	Total gate charge	arge $V_{DD} = 30 \text{ V}, I_D = 40 \text{ A},$		98	-	nC
Qgs	Gate-source charge	V <sub>GS</sub> = 0 to 10 V	-	38	-	nC
$Q_{gd}$	Gate-drain charge	(see Figure 14: "Test circuit for gate charge behavior")	1	28	ı	nC

Table 6: Switching times

The state of the s						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time	$V_{DD} = 30 \text{ V}, I_D = 20 \text{ A},$	-	41	-	ns
tr	Rise time	$R_G = 4.7 \Omega$ , $V_{GS} = 10 V$ (see Figure 13: "Test circuit	-	45	-	ns
t <sub>d(off)</sub>	Turn-off delay time	for resistive load switching	ı	68	-	ns
t <sub>f</sub>	Fall time	times" and Figure 18: "Switching time waveform")	-	35	1	ns

#### Table 7: Source-drain diode

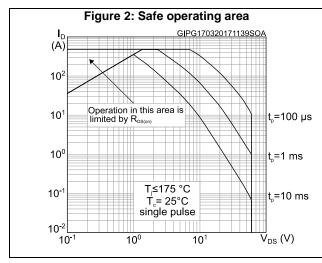
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>SD</sub> <sup>(1)</sup>	Forward on voltage	I <sub>SD</sub> = 40 A, V <sub>GS</sub> = 0 V	ı		1.2	V
t <sub>rr</sub>	Reverse recovery time	$I_D = 40 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	69		ns
Qrr	Reverse recovery charge	$V_{DD} = 48 \text{ V}$	-	103		nC
I <sub>RRM</sub>	Reverse recovery current	(see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	3		А

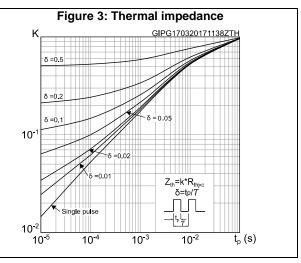
#### Notes:

 $^{(1)}$ Pulsed: pulse duration = 300  $\mu$ s, duty cycle 1.5%



## 2.1 Electrical characteristics (curves)





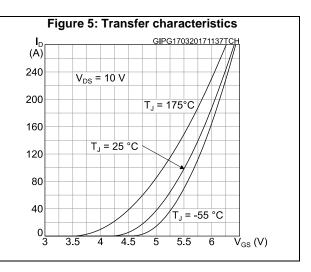
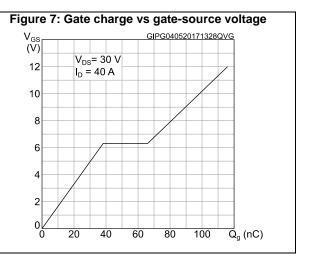
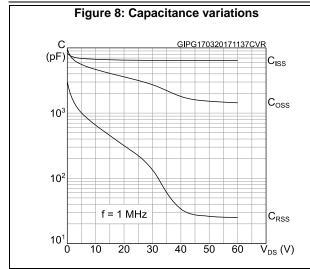
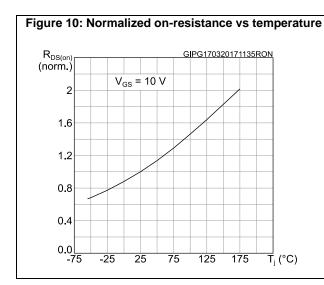
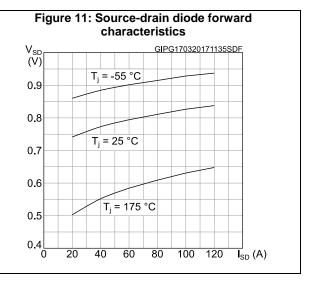


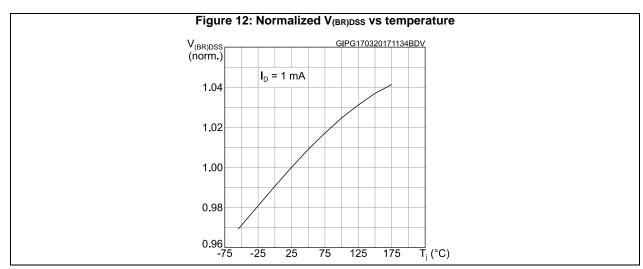
Figure 6: Static drain-source on-resistance  $R_{DS(on)}$  ( $m\Omega$ ) 1.8  $V_{GS} = 10 \text{ V}$  1.6 1.4 1.2 1.0 0.8 0.6 0 20 40 60 80 100 120  $I_D$  (A)











STL220N6F7 Test circuits

### 3 Test circuits

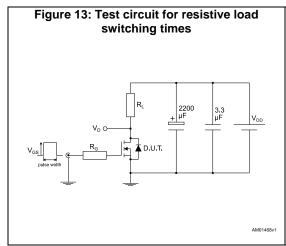
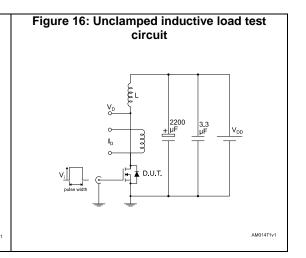


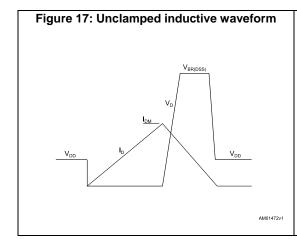
Figure 14: Test circuit for gate charge behavior

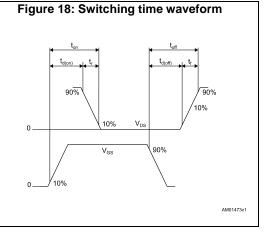
12 V 47 kΩ 100 nF D.U.T.

2200 PF 47 kΩ OVG

AM01466y1







# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

### 4.1 PowerFLAT 5x6 type C package mechanical data

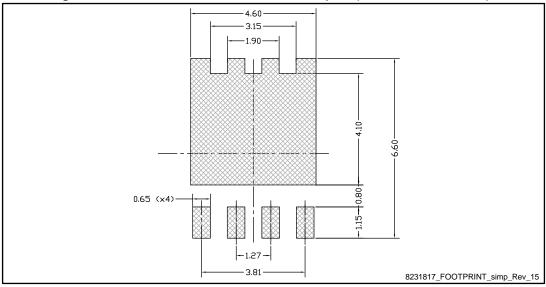
6 7 8  $E_{7}$ E2 E3 Bottom view D5(x4) b(x8) e(x6) Side view Top view 8231817\_typeC\_A0ER\_Rev15

Figure 19: PowerFLAT™ 5x6 type C package outline

Table 8: PowerFLAT™ 5x6 type C package mechanical data

		mm	
Dim.	Min.	Тур.	Max.
А	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
С	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
е		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.75	0.90	1.05
К	1.05		1.35
L	0.725		1.025
L1	0.05	0.15	0.25
θ	0°		12°

Figure 20: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



# 4.2 PowerFLAT 5x6 packaging information

Figure 21: PowerFLAT™ 5x6 tape (dimensions are in mm)

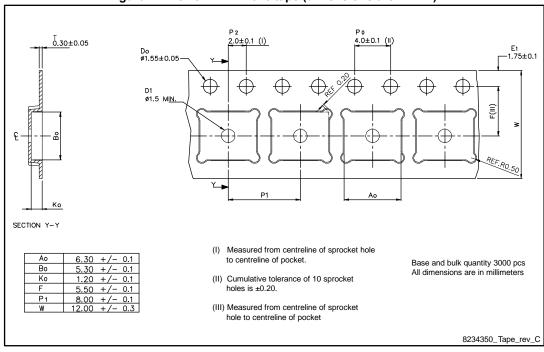
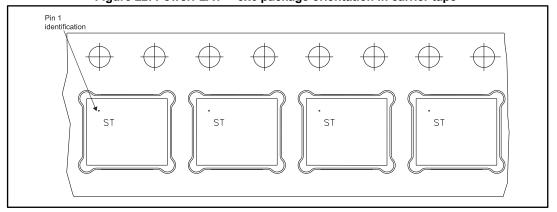


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape



8234350\_Reel\_rev\_C

PART NO.

R25.00

R25.



Revision history STL220N6F7

# 5 Revision history

Table 9: Document revision history

Date	Revision	Changes	
13-Jun-2014	1	First release.	
22-Sep-2014	2	Updated title, features and description in cover page.  Updated Table 2: "Absolute maximum ratings", Table 4: "On /off states", Table 5: "Dynamic", Table 6: "Switching times" and Table 7: "Source-drain diode".  Added Section 3: "Electrical characteristics (curves)".	
14-Jan-2015	3	Document status promoted from preminary to production data.	
02-May-2017	4	Modified title and features table on cover page.  Modified Table 2: "Absolute maximum ratings", Table 4: "On /off states", Table 5: "Dynamic", Table 6: "Switching times" and Table 7: "Source-drain diode".  Modified Section 2.1: "Electrical characteristics (curves)".  Minor text changes.	

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